

Plastic Infrared Emitting Diode

OP266AA, OP266AC, OP266AD



Features:

- T-1 (3 mm) package style
- Narrow irradiance pattern
- Dome lens
- Higher power output than GaAs at equivalent drive currents
- 850 nm LED

Description:

Each device in the **OP266AA** series is a high intensity gallium aluminum arsenide infrared emitting diode (GaAlAs) that is molded in an IR transmissive clear or amber-tinted epoxy package with a dome lens. Devices feature a narrow source irradiance pattern and a variety of electrical characteristics. The small T-1 package style makes these devices ideal for space-limited applications.

These devices are mechanically and spectrally matched to other OPTEK products as follows:

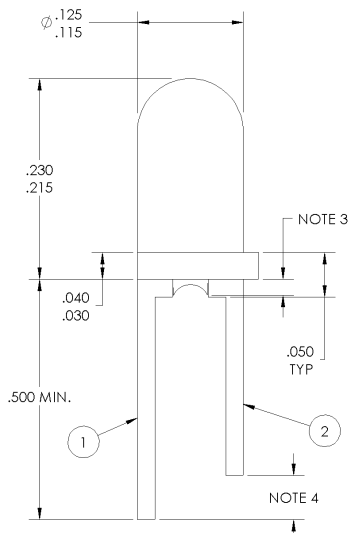
The OP266AA family conform to the OP506 and OP535 series devices.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

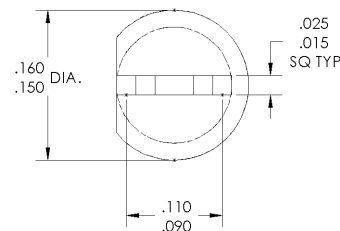
- Space-limited applications
- Applications requiring coupling efficiency
- Battery-operated or voltage-limited applications

Ordering Information					
Part Number	LED Peak Wavelength	Output Power (mW/cm ²) Min / Max	I _F (mA) Typ / Max	Total Beam Angle	Lead Length
OP266AA	850 nm	5.5 / NA	20 / 50	18°	MIN 0.50"
OP266AC		11.5 / 16.5			
OP266AD		15.5 / NA			



NOTES:

1. Outside discrete shell is polysulfone CLEAR.
2. This LED is built with a GaAlAs chip.
3. Max allowable epoxy miniscus is 0.030".
4. For identification purposes, Cathode lead is .065" ± .035" longer than the anode lead.
5. Dimensions are in inches.



Pin #	LED
1	Cathode
2	Anode

CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK's molded plastics.



RoHS

General Note

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Electrical Specifications

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron] ⁽¹⁾	260° C
Power Dissipation ⁽²⁾	100 mW

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Input Diode						
$E_{E(APT)}$	Apertured Radiant Incidence OP266AA OP266AC OP266AD	5.50 11.50 15.50	- - -	- 16.5 -	mW/cm ²	$I_F = 20\text{ mA}$ ⁽³⁾ Aperture = 0.081" diameter Distance = 0.590" from seating surface to aperture surface
V_F	Forward Voltage	1.00	-	1.80	V	$I_F = 20\text{ mA}$
I_R	Reverse Current	-	10	-	μA	$V_R = 10\text{ V}$
λ_p	Wavelength at Peak Emission	-	850	-	nm	$I_F = 10\text{ mA}$
B	Spectral Bandwidth between Half Power Points	-	50	-	nm	$I_F = 20\text{ mA}$
$\Delta\lambda_p / \Delta T$	Spectral Shift with Temperature	-	± 0.18	-	nm/°C	$I_F = \text{Constant}$
θ_{HP}	Emission Angle at Half Power Points	-	18	-	Degree	$I_F = 20\text{ mA}$
t_r	Output Rise Time	-	10	-	ns	$I_{F(PK)} = 100\text{ mA}$, PW = 10 μs , D.C. = 10.0 %
t_f	Output Fall Time	-	10	-	ns	$I_{F(PK)} = 100\text{ mA}$, PW = 10 μs , D.C. = 10.0 %

Notes:

1. RMA flux is recommended. Duration can be extended to 10 second maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
2. Derate linearly at 1.07 mW/° C above 25° C.
3. $E_{E(APT)}$ is a measurement of the average apertured radiant incidence upon a sensing area 0.081" (2.06 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens and 0.590" (14.99 mm) from the measurement surface. $E_{E(APT)}$ is not necessarily uniform within the measured area.

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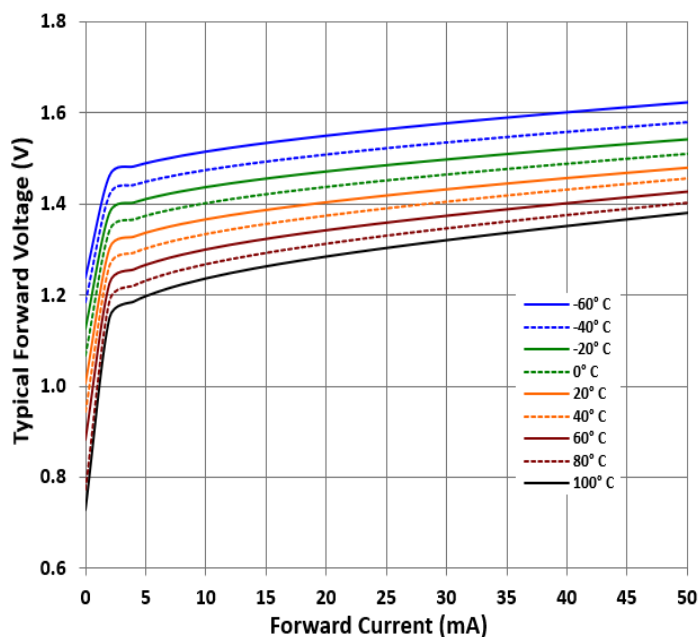
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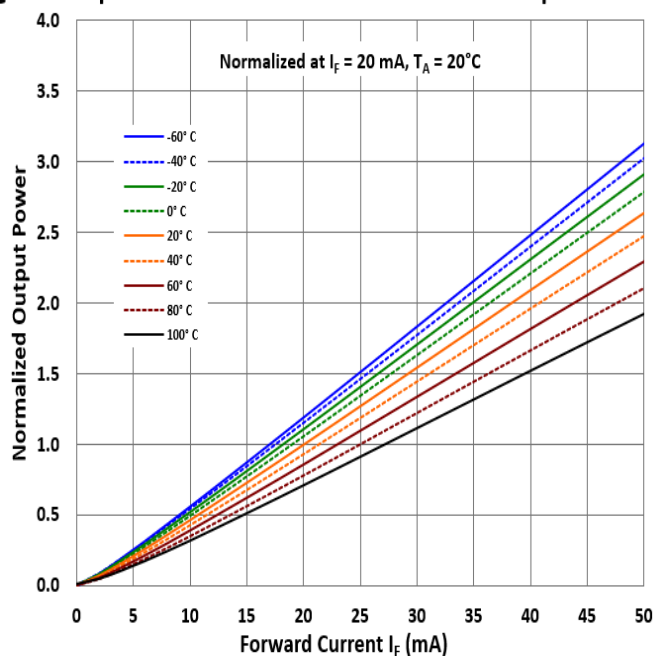
Typical Performance

OP266AA, AC, AD

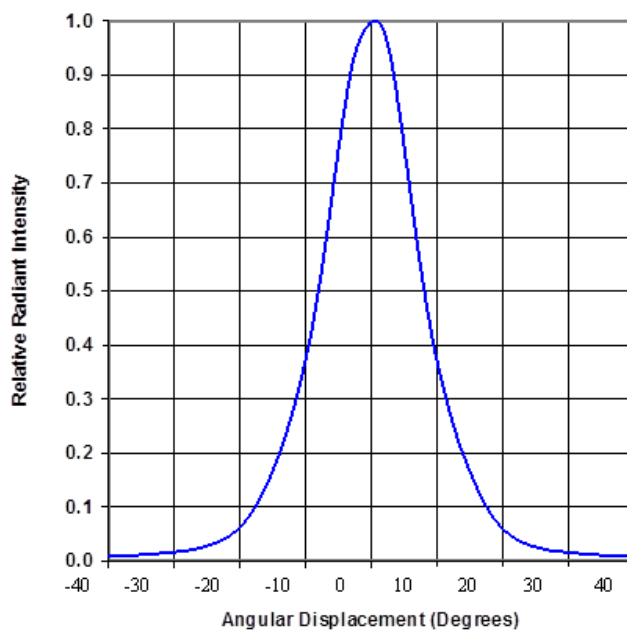
Forward Voltage vs Forward Current vs Temperature



Optical Power vs Forward Current vs Temperature



Relative Radiant Intensity vs. Angular Displacement



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